С		Reg. No. :										
Question Paper Code: 52Q03												
M.E. DEGREE EXAMINATION, APRIL 2019												
Second Semester												
Communication Systems												
15PCM203 – MICROWAVE INTEGRATED CIRCUITS												
(Regulation 2015)												
Dura	Duration: Three hours Maximum: 100 Marks											
Answer ALL Questions												
PART - A (5 x $l = 5$ Marks)												
1.	Lumped element matching networks suitable for frequencies CO1-1)1 - R	
	(a) below 20GHz	(b) below 40GHz	(c) above 40GHz					(d) beyond 100GHz				
2.	Aqua regia is used as etchant for CO2 -I											
	(a) gold (b) platinum (c) platinum alloy							(d) all the above				
3.	The resistivity of SI-GaAs is CO3- R											
4.	(a) $> 10^8 \Omega$ -cm The phase shift offere	(b) $< 10^8 \Omega$ -cm ed by Lange coupler is	(c) >10 ⁶ Ω -cm					(d) $< 10^6 \Omega$ -cm CO4 -R				
	(a) 0°	(b) 45°	(c) 90°				(d) 180°					
5.	The interfacing between time and frequency domain is accomplished							,		CO	05- R	
	(a) DFT (b) FFT (c) IDFT PART $-$ B (5 x 3= 15 Marks)							(d) DCT				
6.	Apply the concept of adaptive beam forming network in conventional satellite CO1-App transmitter.										App	
7.	Explain the process of firing used for fabrication of thick film MICs.									C	0 2- U	
8.	Why dielectric layers are used in MIC technology?							CO3-U				
9.	Explain about high resolution switches with circuit configuration.							CO4-U				
10.	What do you mean by harmonic mixer?						CO5-U					

11. (a) Evaluate the use of MCM technology based on its construction. CO1- U (16)Or (i) Explain the construction of adaptive beam forming network. (b) CO1- U (10)CO1- U (ii) Discuss on various multichip module technologies. (6) 12. (a) Describe in detail about the steps involved in the fabrication of CO2-U (16)thin film MICs with neat block diagram. Or (b) Describe in detail about the fabrication of MICS in which films are CO2- U (16)deposited by evaporation method with necessary diagrams. 13. Explain the processes involved in the growth of dielectric layers. CO3-U (16)(a) Also brief about evaluation of dielectric layer. Or Explain the need and growth of different layers in MMICs and CO3-U (16)(b) mention the materials used for those layers. 14. (a) (i) Explain about construction and use of various MMIC inductors. CO4 -U (10)(ii) Brief about the purpose and use of Microstrip Couplers. CO4 -U (6) Or (b) Discuss in detail about the development of GaAs FET switches CO4-U (16)and its implementation. 15. (i) Explain about amplifier design under conditional stability CO₅-U (8) (a) conditions. (ii) Explain in detail about Low noise amplifier. CO5-U (8) Or (i) Explain in detail about different design approaches of an (b) CO5-U (8) oscillator. (ii) Discuss on CAD techniques for large signal oscillator design. CO5-U (8)

 $PART - C (5 \times 16 = 80 \text{ Marks})$